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EMITTER/COLLECTOR CONTACT TO
DOPED SEMICONDUCTOR WELL AND
RELATED METHODS**(71) Applicant: **GlobalFoundries U.S. Inc.**, Malta, NY
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(57)

ABSTRACT

Embodiments of the disclosure provide a lateral bipolar transistor structure with an emitter/collector (E/C) contact to a doped semiconductor well and related methods. A bipolar transistor structure according to the disclosure may include a doped semiconductor well over a semiconductor substrate. An insulative region is on the doped semiconductor well. A base layer is on the insulative region, and an emitter/collector (E/C) layer on the insulative region and adjacent a first sidewall of the base layer. An E/C contact to the doped semiconductor well includes a lower portion adjacent the insulative region and an upper portion adjacent and electrically coupled to the E/C layer.

